

## APPENDIX

IN THE CLAIMS:

Claims 1, 4, 13-15 and 22 have been amended as follows:

1. (Twice Amended) A method for forming a silicon film, comprising:  
applying by patterning an ink composition containing a silicon compound onto a substrate by an ink jet process, the silicon compound having at least one cyclic structure.

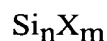
4. (Twice Amended) The method for forming a silicon film according to claim 3, further comprising:

a step for irradiating the silicon film formed by ~~the~~ heat treatment and/or ~~the~~ light treatment with laser to convert the amorphous silicon film into a polycrystalline silicon film.

13. (Twice Amended) The method for forming a silicon film according claim 1, ~~the concentration~~ composition being a viscosity of 1 to 50 mPa·s and a surface tension of 20 to 70 dyn/cm.

14. (Twice Amended) An ink-jet ink composition for forming a silicon film, comprising:

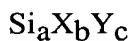
a silicon compound represented



n representing an integer 3 or more, m representing an integer of n, 2n-2, 2n, or 2n+2, and X representing a hydrogen atom and/or a halogen atom, the silicon compound having at least one cyclic structure.

15. (Twice Amended) An ink-jet ink composition for forming a silicon film, comprising:

a silicon compound represented by



X representing a hydrogen atom and/or a halogen atom, Y representing a boron atom or a phosphorus atom, a representing an integer of 3 or more, b representing an integer of a to  $2a+c+2$ , and c representing an integer of 1 to a, the silicon compound having at least one cyclic structure.

22. (Twice Amended) The ink composition according to claim 14, the ~~concentration~~ composition having a viscosity of 1 to 50 mPa·s and a surface tension of 20 to 70 dyn/cm.